

International Rectifier

IRFK3D250, IRFK3F250

Isolated Base Power HEX-pak™ Assembly - Half Bridge Configuration

- High Current Capability.
- UL recognised E78996.
- Electrically Isolated Base Plate.
- Easy Assembly into Equipment.

Description

The HEX-pak™ utilises the well-proven HEXFET™ die, combining low on-state resistance with high transconductance. These superior technology die are assembled by state of the art techniques into the TO-240 package, featuring 2.5kV rms isolation and solid M5 screw connections. The small footprint means the package is highly suited to power applications where space is a premium. Available in two versions, IRFK.D... for fast switching and IRFK.F... for oscillation sensitive applications.

$$V_{DS} = 200V$$

$$R_{DS(on)} = 30m\Omega$$

$$I_D = 70A$$

Absolute Maximum Rating

	Parameter	Max.	Units
$I_D @ T_C = 25^\circ C$	Continuous Drain Current	70	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current	41	A
I_{DM}	Pulse Drain Current	280	A ①
$P_D @ T_C = 25^\circ C$	Maximum Power Dissipation	625	W
V_{GS}	Gate-to-Source Voltage	20	V
V_{INS}	R.M.S. Isolation Voltage, circuit to base	2.5	kV
T_J	Operating Junction Temperature Range	-40 to 150	$^\circ C$
T_{STG}	Storage Temperature Range	-40 to 150	$^\circ C$

Thermal and Mechanical Specifications

	Parameter	Min.	Typ.	Max.	Units
R_{thJC}	Junction-to-Case	-	-	0.20	K/W ②
R_{thCS}	Case-to-Sink, smooth & greased surface	-	0.1	-	K/W
T	Mounting Torque +10%				③
	HEXpak to Heatsink	-	5	-	Nm
	Busbar to HEXpak	-	3	-	Nm
wt	Approximate Weight	-	140	-	g
		-	5	-	oz

Notes:

- ① - Repetitive Rating: Pulse width limited by maximum junction temperature see figure 8.
- ② - Per Module.
- ③ - A mounting compound is recommended and the torque should be rechecked after a period of three hours to allow for the spread of the compound.

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Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (Unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Test Conditions	
B _{VDS}	Drain-to-Source Breakdown voltage	200	-	-	V	V _{GS} =0V, I _D =1.0mA	
R _{DS(on)}	Static Drain-to-Source On-State Resistance	-	24	30	mΩ	V _{GS} =10V, I _D =41A	
I _{D(on)}	On State Drain Current	70	-	-	A	V _{DS} > I _{D(on)} × R _{DS(on)} max, V _{GS} =10V	
V _{GS(th)}	Gate Threshold Voltage	2.0	-	4.0	V	V _{DS} =V _{GS} , I _D =1.0mA	
g _{fs}	Forward Transconductance ④	36	54	-	S	V _{DS} > 50V, I _D =41A	
I _{DSS}	Zero Gate Voltage Drain Current	-	-	0.75	mA	V _{DS} =V _{DS} max, V _{GS} =0v	
		-	-	3.0	mA	V _{GS} =10V, T _C =125°C, V _{DS} =V _{DS} max × 0.8	
I _{GSS}	Gate-to-Source Leakage Forward	-	-	300	nA	V _{GS} =20V	
I _{GSS}	Gate-to-Source Leakage Reverse	-	-	-300	nA	V _{GS} = -20V	
Q _g	Total Gate Charge	-	260	390	nC	I _D =70A, V _{GS} =10V,	
Q _{gs}	Gate-to-Source Charge	-	48	72	nC	V _{DS} =V _{DS} max × 0.8	
Q _{gd}	Gate-to-Drain ("Miller") Charge	-	138	210	nC		
t _{d(on)}	Turn-on Delay Time	IRFK3D250	-	40	-	ns	V _{DD} =95V, I _D =41A,
		IRFK3F250	-	45	-	ns	
t _r	Rise Time	IRFK3D250	-	100	-	ns	V _{GS} =10V,
		IRFK3F250	-	125	-	ns	
t _{d(off)}	Turn-off Delay Time	IRFK3D250	-	160	-	ns	R _{SOURCE} =3.3Ω
		IRFK3F250	-	210	-	ns	
t _f	Fall Time	IRFK3D250	-	50	-	ns	
		IRFK3F250	-	80	-	ns	
L _{DS}	Drain-to-Source Inductance	-	18	-	nH		
C _{iss}	Input Capacitance	-	9.0	-	nF	V _{GS} =0V, V _{DS} =25V,	
C _{oss}	Output Capacitance	-	2.5	-	nF	f=1.0MHz	
C _{rss}	Reverse Transfer Capacitance	-	0.7	-	nF		
	Linear Derating Factor	-	-	5	W/K		

Source-Drain Diode Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Test Conditions
I_S	Continuous Source Current (Body Diode)	-	-	70	A	
I_{SM}	Pulsed Source Current (Body Diode)	-	-	245	A	
V_{SD}	Diode Forward Voltage	-	-	2.0	V	$V_{GS}=0V, I_S=70A, T_C=25^\circ\text{C}$
t_{rr}	Reverse Recovery Time	9160	320	640	ns	$di/dt=400A/\mu s, T_J=150^\circ\text{C}$
Q_{rr}	Reverse Recovered Charge	6.6	13.0	26.0	μC	$I_S=70A$

Notes:

④ - Pulse Width $\leq 300\mu s$; Duty cycle $\leq 2\%$.



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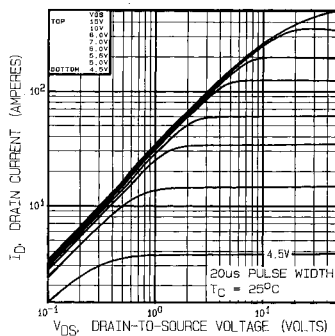


Fig 1. Typical Output Characteristics,
 $T_C=25^\circ\text{C}$

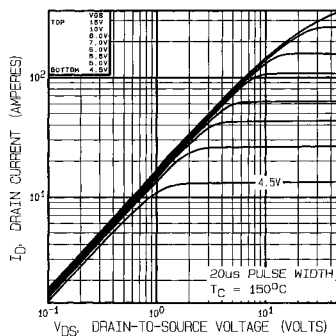


Fig 2. Typical Output Characteristics,
 $T_C=150^\circ\text{C}$

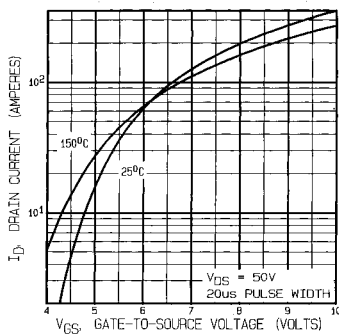


Fig 3. Typical Transfer Characteristics

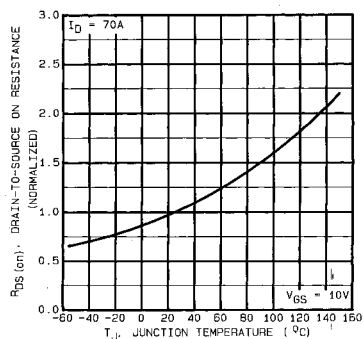


Fig 4. Normalized On-Resistance Vs.
Temperature

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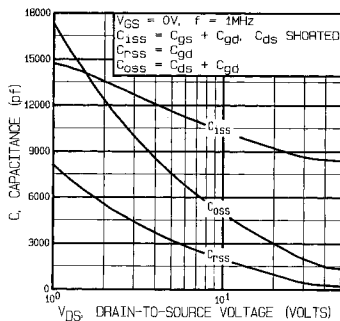


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

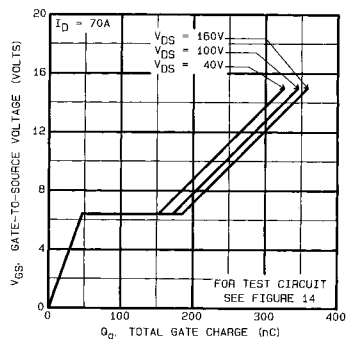


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

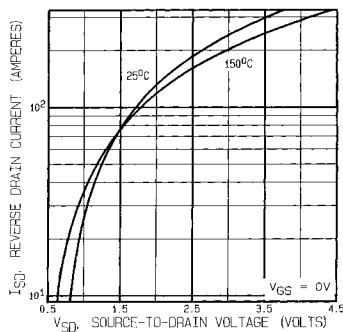


Fig 7. Typical Source-Drain Diode Forward Voltage

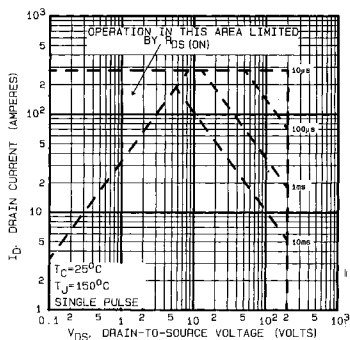


Fig 8. Maximum Safe Operating Area

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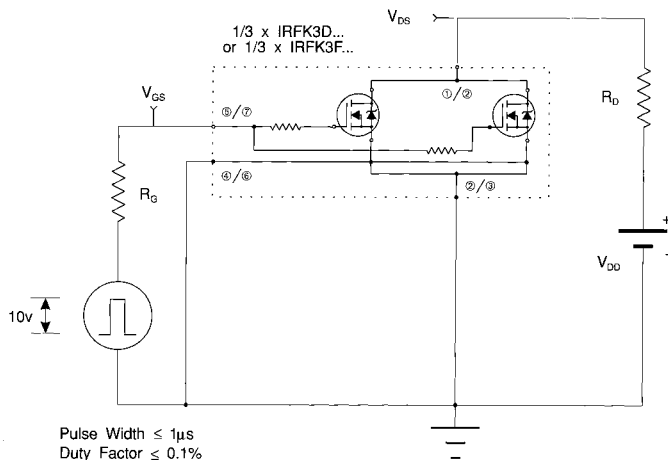


Fig 11a. Switching Time Test Circuit

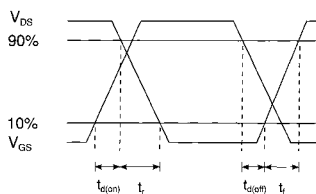


Fig 11b. Switching Time Waveforms

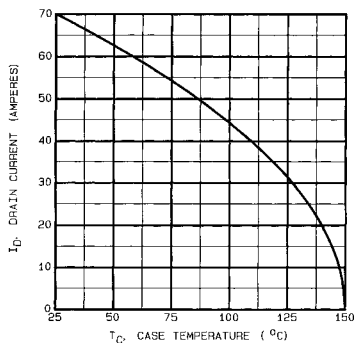


Fig 9. Maximum Drain Current Vs. Case Temperature

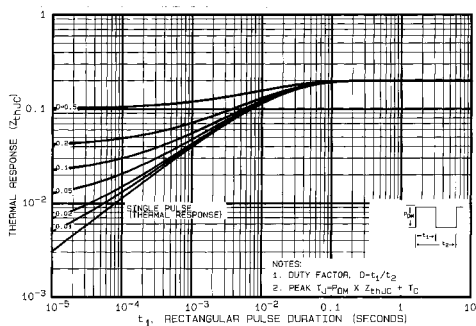
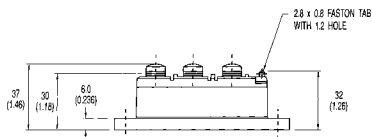
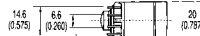
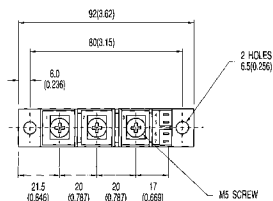
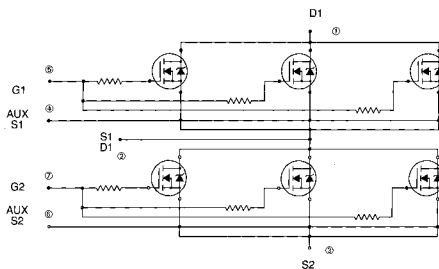


Fig 10. Maximum Effective Transient Thermal Impedance, Junction-to-Case



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Circuit Configuration and Outline



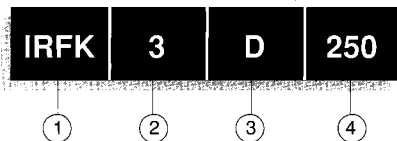
NOTE:
DEVICE IS SUPPLIED WITH
AUXILIARY LEADS 200(7.87) LONG

All dimensions in millimetres (inches)

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Part Numbering



1. - HEX-pak Module.
2. - Number of arms of bridge.
3. - D - Fast switching.
F - Oscillation resistant for sensitive applications.
4. - Voltage code:-
054 - 60V
150 - 100V
250 - 200V
350 - 400V
450 - 500V
C50 - 600V

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In the interest of product improvement INTERNATIONAL RECTIFIER reserves the right to change specifications at any time without notice.

MJW/1/92